

AVL Software and Functions GmbH

AVL e-Drive

Air cooled Power electronic design PDiM 2018 Sweden - Göteborg

F. Haag, S. Pruefling



Full solution offering from concept, components to fully integrated E-Drive systems



Cooling of power electronics is a system topic



AVL e-Drive Cooling solutions for power electronics in today's use



Source: electronics-cooling Natural and forced convection air cooled head sinks



Jet impingement and direct contact liquid cooling of module base plates or DBC substrates



Single and double sided cooling with liquid cold plates



Micro-channel liquid coolers built into power module base plates or integrated with the DBC substrate



Source: luscombe

Two-phase liquid cold plates with boiling of dielectric refrigerant coolant

High potential of air cooling for lower system complexity and cost reduction



Cost benefit and reduction on system level

Natural or forced air cooling has several benefits such as...

- No leakage compared to liquid cooling possible
- Good integration possibilities especially in (P)HEVs because of no interfacing of existing cooling system necessary

Todays vehicles are indirect air cooled (heat exchanger)









AVL e-Drive What package of semiconductors for air cooling?



Especially for air cooling discrete semiconductors supports better equal heat distribution

AVL e-Drive Design options for power electronic boards for air cooling

Typical thermal connection



PCB

Integration of busbars possible \rightarrow cooling of busbars

Alternative thermal connection

Thermal design also effects the PCB design and layout

AVL e-Drive

What type of semiconductor technology? Advantages of SiC for air cooling



At a switching frequency similar to current IGBT inverter applications a SiC Converter shows

AVL

- Lower losses -> less internal temperature increase AND
- Better thermal conductivity
- Accepts higher junction temperature up to 200°C



SiC has better thermal properties and therefore big advantages for air cooled applications

AVL e-Drive Air cooling example: 800V SiC Inverter for auxiliary applications







- Development of 800V SiC inverter for auxiliary components like e-charger, e-compressor
- Design to Cost
- Separated Control and Powerboard for better EMC-charcteristics
- Key specifications
 - No. of phases
 - V_{DC}
 - V_{nom}
 - Pout, max
 - Inom

3 485-920V 800V 22kW 15A_{rms}

AVL e-Drive Semiconductor loss calculation

- Loss simulation based on critical load points
- Mosfet model from supplier for simulation





Inverter conductive losses are defined as:

$$P_{loss,conductive} = I^2 R_{DSon} + 2\left(\frac{l}{2}\right)^2 R_{DSon}$$

Inverter switching losses are defined as:

$$P_{loss,switching} = 6f_{PWM}(E_{on} + E_{off})$$

Total losses of Inverter:

$$P_{loss,total} = I^2 R_{DSon} + 2\left(\frac{I}{2}\right)^2 R_{DSon} + 6f_{PWM}(E_{on} + E_{off})$$

Mean value of losses per Mosfet:

$$P_{loss,Mosfet} = \frac{1}{2}I^2 R_{DSon} + f_{PWM} (E_{on} + E_{off})$$

AVL e-Drive Thermal model of inverter





- Heat transfer coefficent of the housing: $HTC = 10 \frac{W}{m^2 K}$, (free convection)
- Ambient temperature: $T_{ambient} = 20^{\circ}C$
- Gappad (Kerafol U90 s=0,2mm): $d = 0.2mm, k = 6 \frac{W}{mK}$
- Housing (AlMg4.5Mn0.7 EN AW 5083): $k = 125 \frac{W}{mK}$
- R_{mosfet}: 0.55 °C/W (junction-case resistance)







- Max. power at 200°C junction temperature is 26.4kW based on the numerical simulation
- The Mosfet's have a power losses of 270W
- Max. surface temperature of Gappad is 176 °C.







Max. temperature at the Gappad is 79 °C and 138 °C for 10 and 20 kW module power

- The corresponding junction temperature is 88.2 °C at 10 kW and 156 °C at 20 kW
- The average surface temperature is for 10 and 20 kW module power a surface temperature of 76 °C and 131 °C.

For the planned operating performances, the power module is at a safe distance from its max. allowed limit temperature

Max, temperature at the Gappad is **79** °C





AVL e-Drive

Results of the thermal simulation and influence of module power



AVL e-Drive Results of the thermal simulation and influence of module power

 Investigation of different HTCs: 10 W/m²-K (free convection) 50 W/m²-K (low air flow) 150 W/m²-K (High air flow)

26.4 kW 56.1 kW 72.8 kW

 Erhaltene Equations for module power and max. temperature of gappad:

 $P_{Module} = 13.541 \cdot HTC^{0.341}$ $T_{Max_{if}} = 222.841 \cdot HTC^{-0.103}$

The air flow has the biggest impact for the max. possible power of the inverter



AVL e-Drive Air cooled Example: 48V Crosscharger

- For the ideal vorticity (turbulent air flow) of the air the housing is designed as "pin fin"
- 4 parallel Mosfets per single switch









